



### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
001/	2Ω @ V <sub>GS</sub> = 4V	407mA
60V	2.5Ω @ V <sub>GS</sub> = 2.5V	364mA

# **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

- **DC-DC Converters**
- **Power Management Functions**
- Battery Operated Systems and Solid-State Relays

### **Mechanical Data**

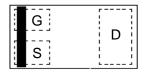
- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.001 grams (Approximate)



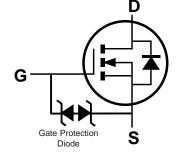




**Bottom View** 



Top View Pin-Out



**Equivalent Circuit** 

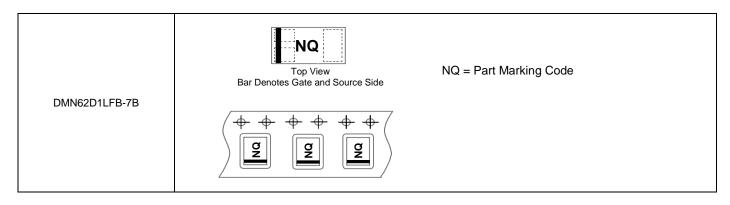
### Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DMN62D1LFB-7B	NO	7	8	10.000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**





### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characte	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	60	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	407 325	mA
Pulsed Drain Current (Note 6)	I <sub>DM</sub>	1	Α		

# **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	0.5	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>ÐJA</sub>	251	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

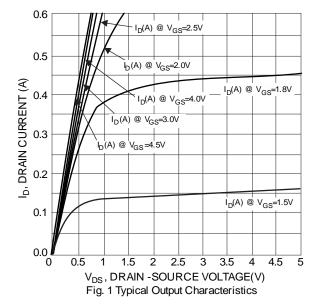
# Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise stated.)

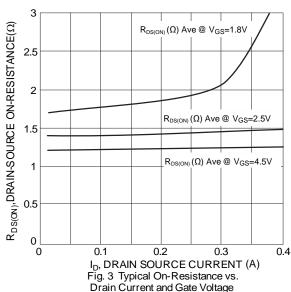
	_						
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>		_	1.0	μΑ	$V_{DS} = 60V$ , $V_{GS} = 0V$	
			_	±100	nA	$V_{GS} = \pm 5V$ , $V_{DS} = 0V$	
Gate-Source Leakage	$I_{GSS}$	_	_	±500	nA	$V_{GS} = \pm 10V$ , $V_{DS} = 0V$	
			_	±2.0	μA	$V_{GS} = \pm 15V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.6	_	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
		l	1.3	2		$V_{GS} = 4V, I_D = 100mA$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		1.5	2.5	Ω	$V_{GS} = 2.5V, I_D = 50mA$	
	, ,		1.9	3		$V_{GS} = 1.8V, I_D = 50mA$	
Diode Forward Voltage	$V_{SD}$		0.9	1.3	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>		32	64		V 05V V 0V	
Output Capacitance	Coss	l	4.4	9	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		2.9	6		1 – 1.000112	
Gate Resistance	$R_{g}$	l	126	250	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	$Q_g$		0.45	0.9		$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 250 \text{mA}$	
Gate-Source Charge	$Q_{gs}$		0.08	0.2	nC		
Gate-Drain Charge	$Q_{gd}$		0.08	0.2			
Turn-On Delay Time	t <sub>D(ON)</sub>	1	3.4	10	ns	$V_{GS} = 10V, V_{DS} = 30V,$ $R_{L} = 150\Omega, R_{G} = 25\Omega,$ $I_{D} = 200\text{mA}$	
Turn-On Rise Time	t <sub>R</sub>	1	3.4	10	ns		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	ı	26.4	45	ns		
Turn-Off Fall Time	t <sub>F</sub>		16.3	30	ns		

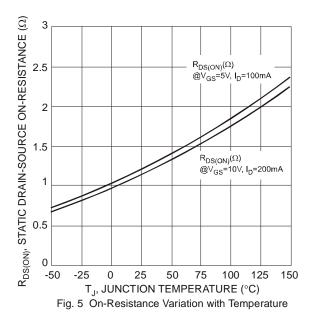
Notes:

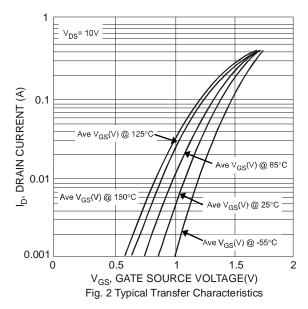
- 5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
- Repetitive rating, pulse width limited by junction temperature.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to production testing.

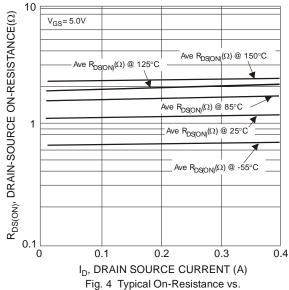












Drain Current and Temperature

1.6 V<sub>TH</sub> (V) @ I<sub>D</sub>=1mA

(S) 1.4 BUT 1.2

1.2 0.8 BUT 1.2 0.8

1.4 BUT 1.2 0.8

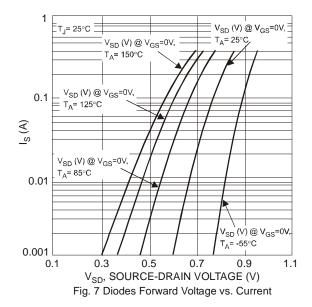
1.5 0.4 0.2

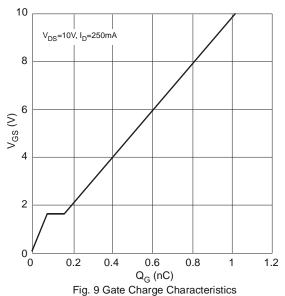
1.5 0 0.2 0.2 50 75 100 125 15

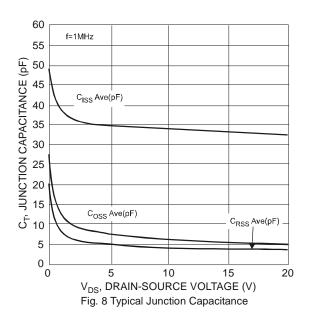
T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

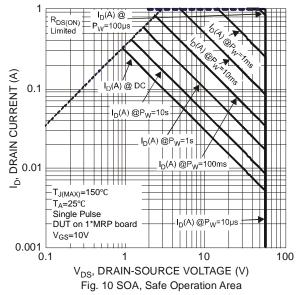
Fig. 6 Gate Threshold Variation vs. Junction Temperature

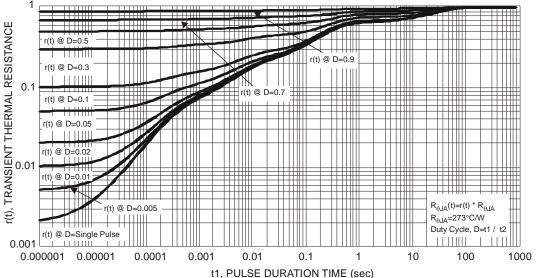










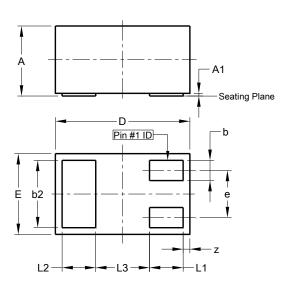




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X1-DFN1006-3

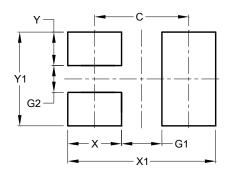


X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е	ı	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	-	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X1-DFN1006-3



Dimensions	Value (in mm)			
С	0.70			
G1	0.30			
G2	0.20			
Х	0.40			
X1	1.10			
Y	0.25			
Y1	0.70			



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